WR0553I ṂṂÞ QSQ ÆṀ ч s ‖ ㄱ Silicon NPN transistor in a TO-220F Plastic Package.

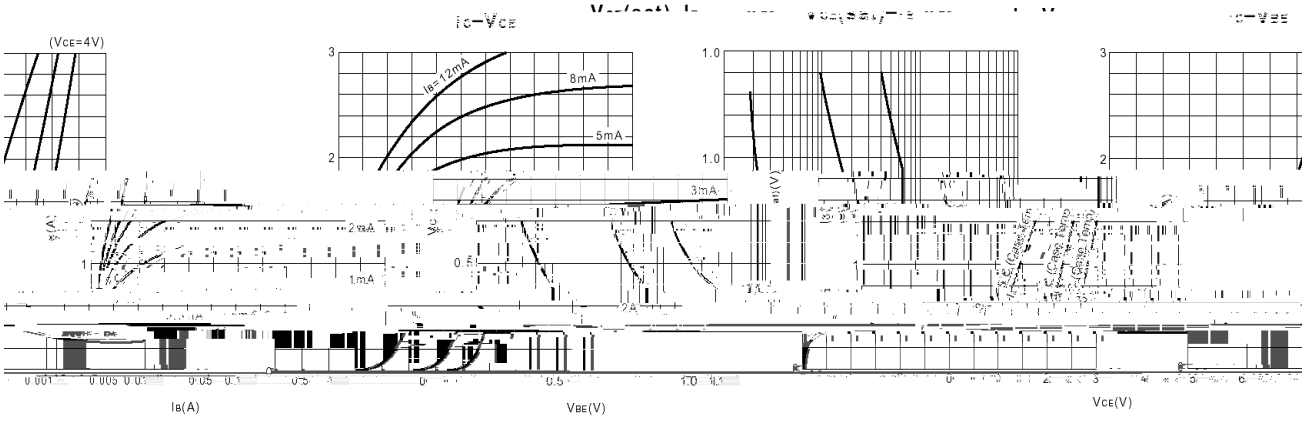
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High h_{FE}, low V

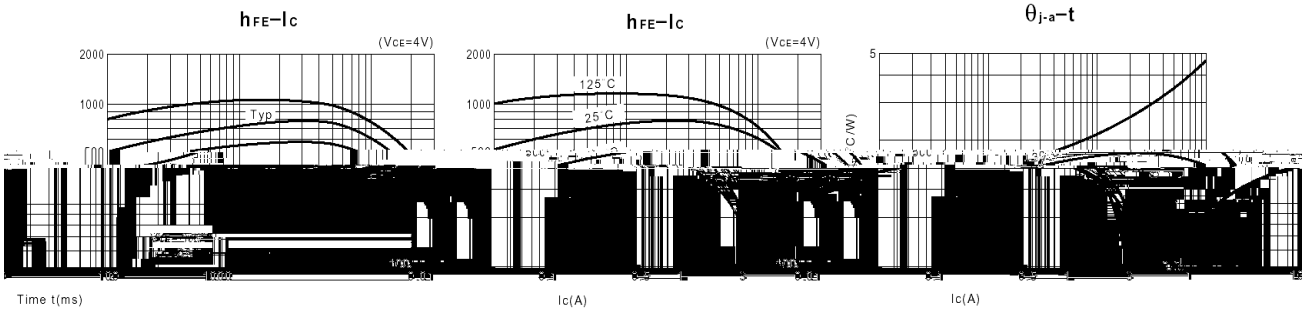
v ̈Ω Parameter	ϒ N Symbol	̈Ω Ö Rating	D Ч Unit
Collector to Base Voltage	V_{CBO}	80	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	3.0	A
Base Current	I_B	1.0	A
Collector Power Dissipation	P_C(Tc=25)	25	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

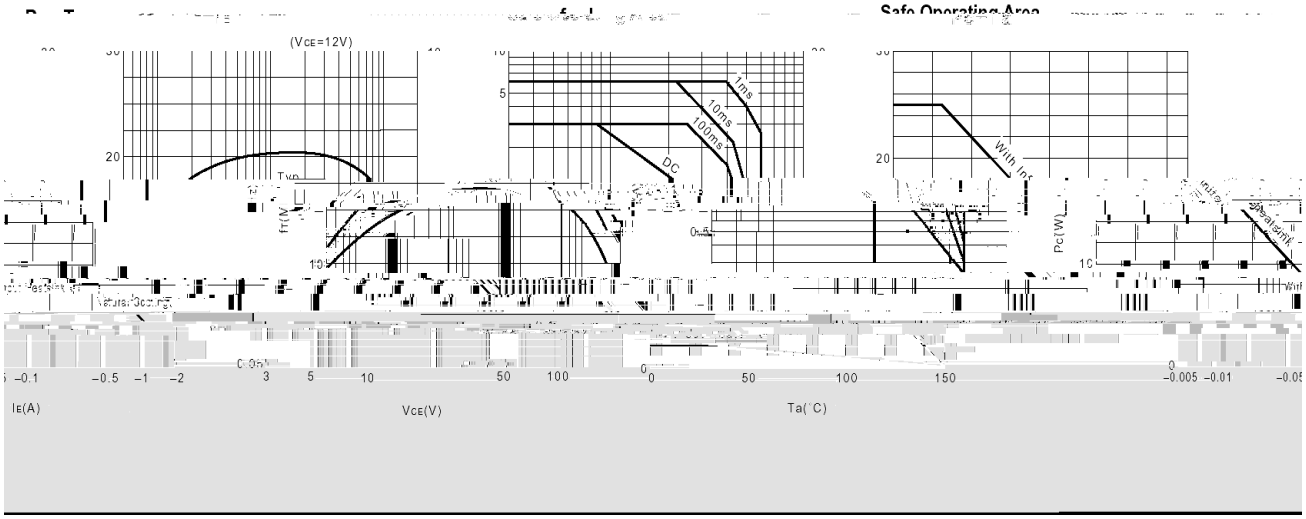
v ̈Ω Parameter	ϒ N Symbol	Ш ː ̊ Ţ Test Conditions	ώ ṇ Ö Min	Ɛ ʒ Ö Typ	ώ ᶻ Ö Max	D Ч Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=25mA	60			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=80V I_E=0			10	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=6.0V I_C=0			100	μA
DC Current Gain	h_{FE}	V_{CE}=4.0V I_C=500mA	500		2000	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=2.0A I_B=50mA			0.5	V
Transition Frequency	f_T	V_{CE}=12V I_C=0.2A		15		MHz

18.48 ref 18.48 refBT10.5 0 0 10.5 55.98114998 243 0 151]TJ(f)6(cit)9TJce84.268-301C-0.004 Tc0 Tw(T)Tj181 00.4

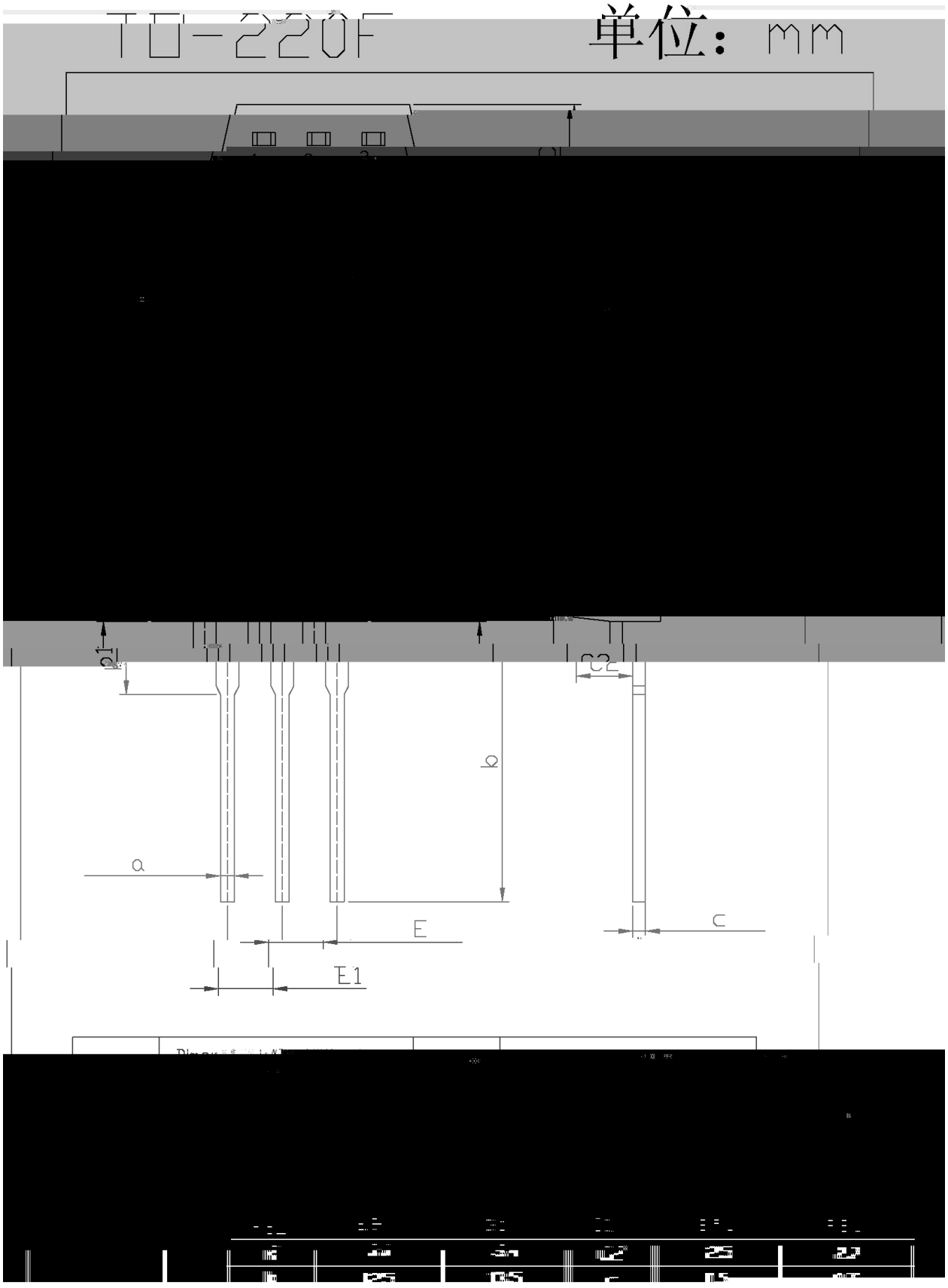
/ Electrical Characteristic Curve



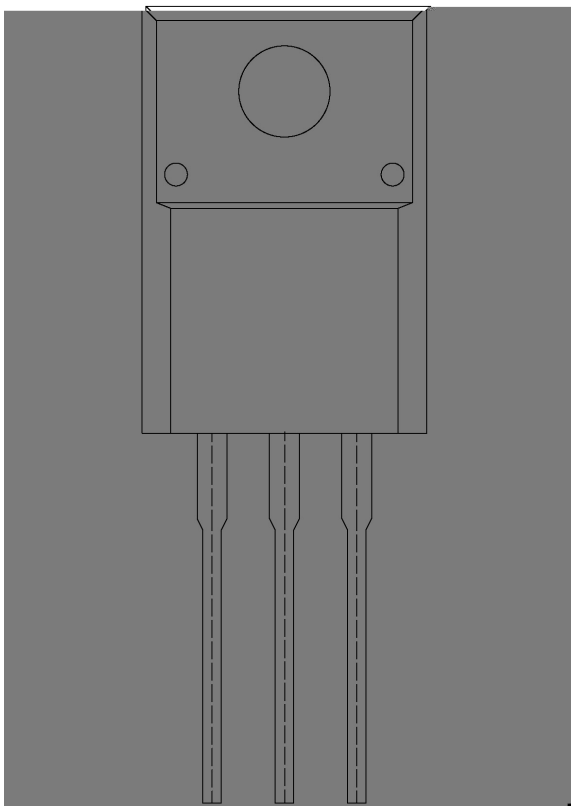




/ Package Dimensions



/ Marking Instructions



ِ ّ χ

EU χ ѭ ϳ и Ґђ

F6 ; 85 χ ѭ ϲ N Ґђ